

# 250 mA, Ultra-Low Noise and High PSRR LDO Regulator for RF and Analog Circuits

# **SCV8163**

The SCV8163 is a next generation of high PSRR, ultra-low noise LDO capable of supplying 250 mA output current. Designed to meet the requirements of RF and sensitive analog circuits, the SCV8163 device provides ultra-low noise, high PSRR and low quiescent current. The device also offer excellent load/line transients. The SCV8163 is designed to work with a 1  $\mu F$  input and a 1  $\mu F$  output ceramic capacitor. It is available in XDFN4 0.65P, 1 mm x 1 mm package.

#### **Features**

- Operating Input Voltage Range: 2.2 V to 5.5 V
- Available in Fixed Voltage Option: 1.2 V to 5.3 V
- ±2% Accuracy Over Load/Temperature
- Ultra Low Quiescent Current Typ. 12 μA
- Standby Current: Typ. 0.1 μA
- Very Low Dropout: 80 mV at 250 mA @ 3.3 V
- Ultra High PSRR: Typ. 92 dB at 20 mA, f = 1 kHz
- Ultra Low Noise: 6.5 μV<sub>RMS</sub>
- Stable with a 1 μF Small Case Size Ceramic Capacitors
- Available in XDFN4 1 mm x 1 mm x 0.4 mm Package
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; Grade 1 AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### **Typical Applications**

- ADAS, Infotainment & Cluster, and Telematics
- General Purpose Automotive & Industrial
- Building & Factory Automation, Smart Meters

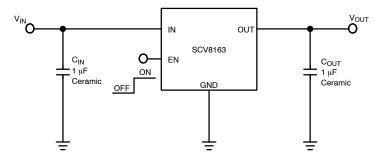


Figure 1. Typical Application Schematics

# MARKING DIAGRAM

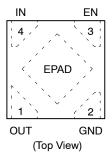


XDFN4 CASE 711AJ



XX = Specific Device Code M = Date Code

#### **PIN CONNECTIONS**



#### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 14 of this data sheet.

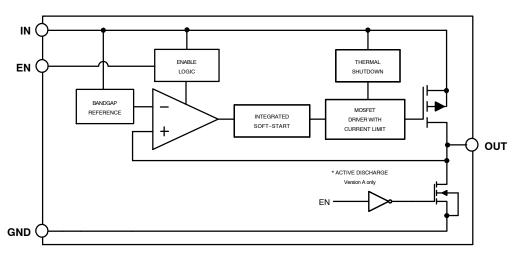


Figure 2. Simplified Schematic Block Diagram

#### **PIN FUNCTION DESCRIPTION**

Pin No.	Pin Name	Description				
4	IN	Input voltage supply pin				
1	OUT	egulated output voltage. The output should be bypassed with small 1 μF ceramic capacitor.				
3	EN	Chip enable: Applying $V_{EN}$ < 0.4 V disables the regulator, Pulling $V_{EN}$ > 1.0 V enables the LDO.				
2	GND	Common ground connection				
-	N/C	Not connected. This pin can be tied to ground to improve thermal dissipation.				
EP	EPAD	Exposed Pad. Exposed pad can be tied to ground plane for better power dissipation.				

#### **ABSOLUTE MAXIMUM RATINGS**

Rating	Symbol	Value	Unit	
Input Voltage (Note 1)	V <sub>IN</sub>	–0.3 V to 6	V	
Output Voltage	V <sub>OUT</sub>	-0.3 to V <sub>IN</sub> + 0.3, max. 6 V	V	
Chip Enable Input	V <sub>CE</sub>	–0.3 to 6 V	V	
Output Short Circuit Duration	t <sub>SC</sub>	unlimited	s	
Operating Ambient Temperature Range	T <sub>A</sub>	-40 to +125	°C	
Maximum Junction Temperature	T <sub>J</sub>	150	°C	
Storage Temperature Range	T <sub>STG</sub>	−55 to +150	°C	
ESD Capability, Human Body Model (Note 2)	ESD <sub>HBM</sub>	2000	V	
ESD Capability, Machine Model (Note 2)	ESD <sub>MM</sub>	200	V	
ESD Capability, Charged Device Model (Note 2)	ESD <sub>CDM</sub>	1000	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
- 2. This device series incorporates ESD protection and is tested by the following methods:
  - ESD Human Body Model tested per EIA/JESD22-A114
  - ESD Machine Model tested per EIA/JESD22-A115
  - ESD Charged Device Model tested per EIA/JESD22-C101, Field Induced Charge Model
  - Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

### **RECOMMENDED OPERATING CONDITIONS**

Rating	Symbol	Min	Max	Unit
Input Voltage	$V_{IN}$	2.2	5.5	V
Junction Temperature	$T_{J}$	-40	+125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Characteristics, XDFN4 (Note 3), Thermal Resistance, Junction-to-Air	$R_{\theta JA}$	198.1	°C/W

<sup>3.</sup> Measured according to JEDEC board specification. Detailed description of the board can be found in JESD51-7

 $\textbf{ELECTRICAL CHARACTERISTICS} - 40^{\circ}C \leq T_{J} \leq 125^{\circ}C; \ V_{IN} = V_{OUT(NOM)} + 1 \ V; \ I_{OUT} = 1 \ \text{mA}, \ C_{IN} = C_{OUT} = 1 \ \mu\text{F}, \ unless otherwise}$ noted.  $V_{EN} = 1.0 \text{ V}$ . Typical values are at  $T_J = +25^{\circ}\text{C}$  (Note 4).

Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage			V <sub>IN</sub>	2.2		5.5	V
Output Voltage Accuracy	$V_{IN} = (V_{OUT(NOM)} + 1 \text{ V}) \text{ to } 5.5 \text{ V}$		V <sub>OUT</sub>	-2		+2	%
	V <sub>IN</sub> = (V <sub>OUT</sub> (NOM) (for V <sub>OUT</sub>	+ 1 V) to 5.5 V < 1.8 V)	V <sub>OUT</sub>	-3		+3	%
Line Regulation	V <sub>OUT(NOM)</sub> + 1 \	′ ≤ V <sub>IN</sub> ≤ 5.5 V	Line <sub>Reg</sub>		0.02		%/V
Load Regulation	I <sub>OUT</sub> = 1 mA	to 250 mA	Load <sub>Reg</sub>		0.001	0.005	%/mA
Dropout Voltage (Note 5)	I <sub>OUT</sub> = 250 mA	V <sub>OUT(NOM)</sub> = 1.8 V	$V_{DO}$		180	250	mV
		V <sub>OUT(NOM)</sub> = 2.8 V			95	160	1
		V <sub>OUT(NOM)</sub> = 3.0 V			90	155	1
		V <sub>OUT(NOM)</sub> = 3.3 V			80	145	1
Output Current Limit	V <sub>OUT</sub> = 90%	V <sub>OUT(NOM)</sub>	I <sub>CL</sub>	250	700		mA
Short Circuit Current	V <sub>OUT</sub> =	= 0 V	I <sub>SC</sub>		690		1
Quiescent Current	I <sub>OUT</sub> = (	0 mA	IQ		12	20	μΑ
Shutdown Current	V <sub>EN</sub> ≤ 0.4 V, '	V <sub>IN</sub> = 4.8 V	I <sub>DIS</sub>		0.01	1	μΑ
EN Pin Threshold Voltage	EN Input Vo	$V_{ENH}$	1.0			V	
	EN Input Vo	oltage "L"	$V_{ENL}$			0.4	1
EN Pull Down Current	V <sub>EN</sub> = 4.8 V		I <sub>EN</sub>		0.2	0.5	μΑ
Turn-On Time	$C_{OUT}$ = 1 $\mu$ F, From assertion of $V_{EN}$ to $V_{OUT}$ = 95% $V_{OUT(NOM)}$				120		μs
Power Supply Rejection Ratio	I <sub>OUT</sub> = 20 mA		PSRR		91 92 85 60		dB
Output Voltage Noise	f = 10 Hz to 100 kHz	I <sub>OUT</sub> = 1 mA I <sub>OUT</sub> = 250 mA	V <sub>N</sub>		8.0 6.5		μV <sub>RMS</sub>
Thermal Shutdown Threshold	Temperature rising		T <sub>SDH</sub>		160		°C
	Temperatu	$T_{SDL}$		140		°C	
Active Output Discharge Resistance	V <sub>EN</sub> < 0.4 V, Version A only		R <sub>DIS</sub>		280		Ω
Line Transient (Note 6)	$V_{IN} = (V_{OUT(NOM)} + 1 \text{ V}) \text{ to } (V_{OUT(NOM)} + 1.6 \text{ V})$ in 30 µs, $I_{OUT} = 1 \text{ mA}$		Tran <sub>LINE</sub>	-1			mV
	$V_{IN} = (V_{OUT(NOM)} + 1.6 \text{ V}) \text{ to } (V_{OUT(NOM)} + 1 \text{ V})$ in 30 $\mu$ s, $I_{OUT} = 1 \text{ mA}$					+1	
Load Transient (Note 6)	I <sub>OUT</sub> = 1 mA to 200 mA in 10 μs		Tran <sub>LOAD</sub>	-40			mV
	I <sub>OUT</sub> = 200 mA to		_		+40		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T<sub>A</sub> = 25°C. Low duty cycle pulse techniques are used during the testing to maintain the junction temperature as close to ambient as possible.
 Dropout voltage is characterized when V<sub>OUT</sub> falls 100 mV below V<sub>OUT(NOM)</sub>.

<sup>6.</sup> Guaranteed by design.

# TYPICAL CHARACTERISTICS

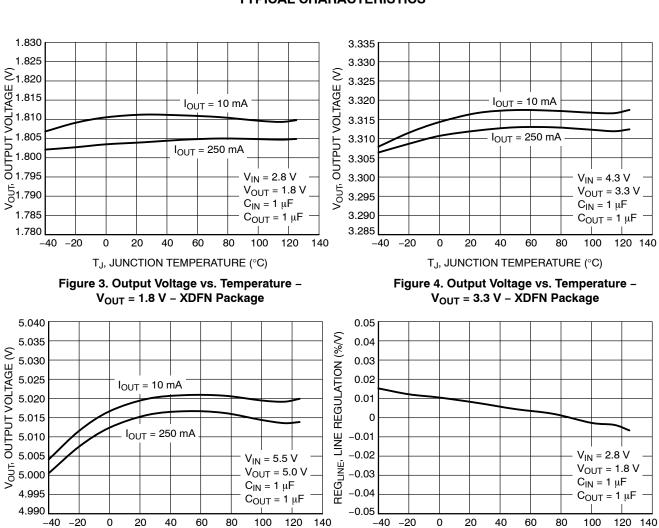


Figure 5. Output Voltage vs. Temperature -V<sub>OUT</sub> = 5.0 V - XDFN Package

T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

100

120

140

-40

0

Figure 6. Line Regulation vs. Temperature -**V<sub>OUT</sub>** = 1.8 **V** 

T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

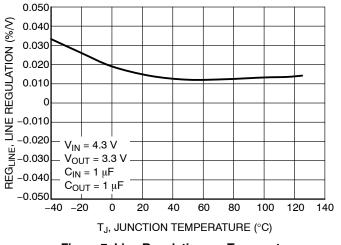


Figure 7. Line Regulation vs. Temperature - $V_{OUT} = 3.3 V$ 

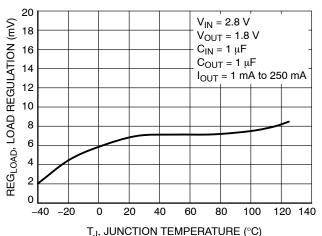


Figure 8. Load Regulation vs. Temperature -**V<sub>OUT</sub>** = 1.8 **V** 

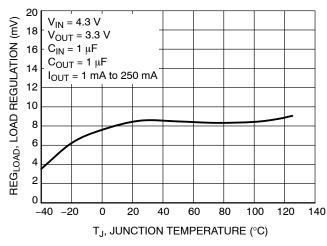


Figure 9. Load Regulation vs. Temperature –  $V_{OUT} = 3.3 \text{ V}$ 

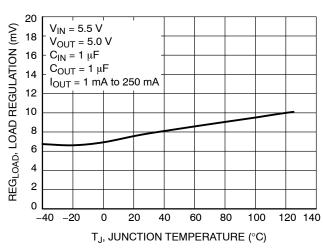


Figure 10. Load Regulation vs. Temperature – V<sub>OUT</sub> = 5.0 V

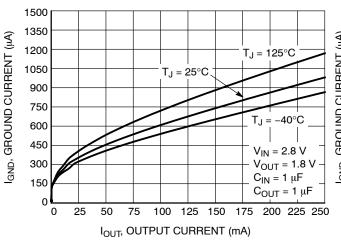


Figure 11. Ground Current vs. Load Current –  $V_{OUT} = 1.8 \text{ V}$ 

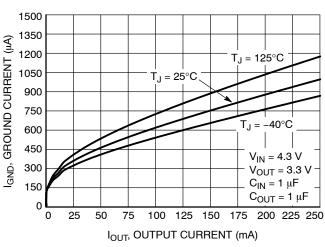


Figure 12. Ground Current vs. Load Current –  $V_{OUT} = 3.3 \text{ V}$ 

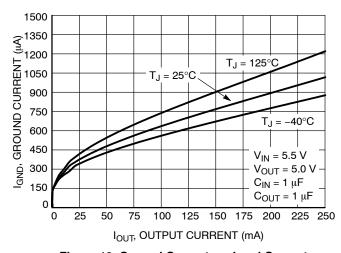


Figure 13. Ground Current vs. Load Current –  $V_{OUT}$  = 5.0 V

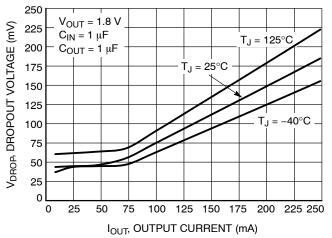


Figure 14. Dropout Voltage vs. Load Current – V<sub>OUT</sub> = 1.8 V – XDFN4 Package

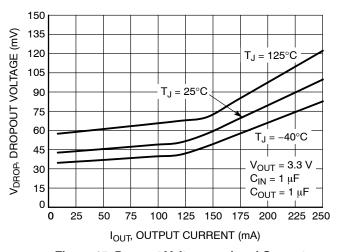


Figure 15. Dropout Voltage vs. Load Current – V<sub>OUT</sub> = 3.3 V – XDFN4 Package

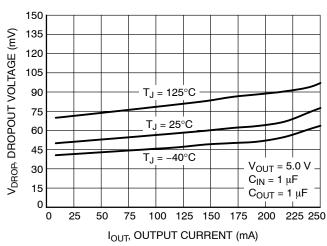


Figure 16. Dropout Voltage vs. Load Current – V<sub>OUT</sub> = 5.0 V – XDFN4 Package

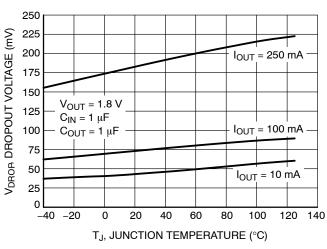


Figure 17. Dropout Voltage vs. Temperature – V<sub>OUT</sub> = 1.8 V – XDFN4 Package

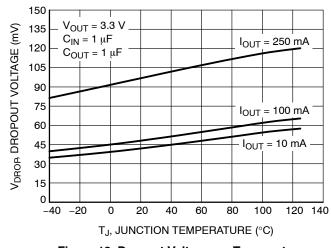


Figure 18. Dropout Voltage vs. Temperature – V<sub>OUT</sub> = 3.3 V – XDFN4 Package

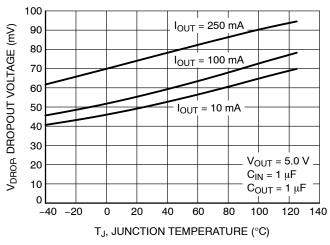


Figure 19. Dropout Voltage vs. Temperature –  $V_{OUT} = 5.0 \text{ V} - \text{XDFN4 Package}$ 

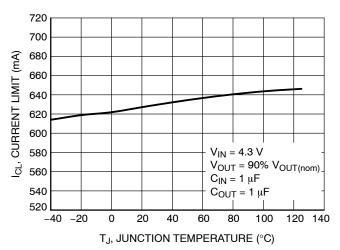
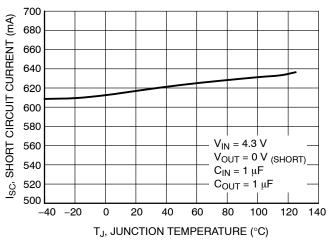


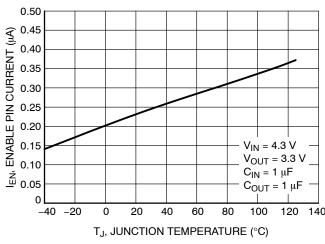
Figure 20. Current Limit vs. Temperature



V<sub>EN</sub>, ENABLE VOLTAGE THRESHOLD (V) 1.0 0.9 0.8 0.7 OFF -> ON 0.6 ON -> OFF 0.5 0.4  $V_{IN} = 4.3 \text{ V}$ 0.3  $V_{OUT} = 3.3 V$ 0.2  $C_{IN}$  = 1  $\mu$ F 0.1  $C_{OUT} = 1 \mu F$ -40 -20 20 100 120 140 40 60 80 T.J., JUNCTION TEMPERATURE (°C)

Figure 21. Short Circuit Current vs. Temperature

Figure 22. Enable Thresholds Voltage



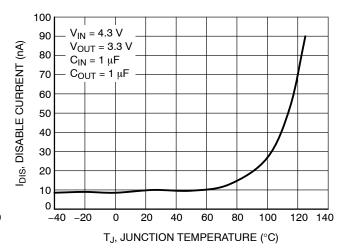
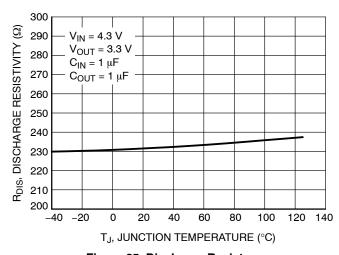


Figure 23. Current to Enable Pin vs. Temperature

Figure 24. Disable Current vs. Temperature



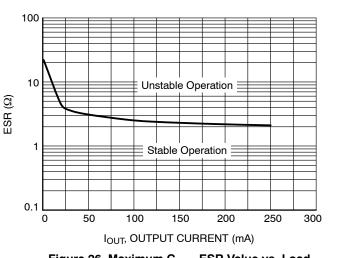
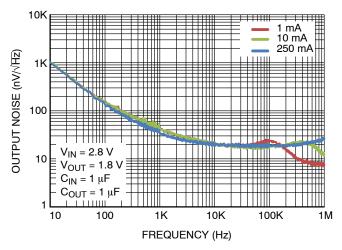


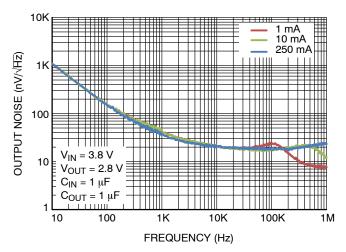
Figure 25. Discharge Resistance vs. Temperature

Figure 26. Maximum  $C_{OUT}$  ESR Value vs. Load Current



	RMS Output Noise (μV)			
lout	10 Hz – 100 kHz	100 Hz – 100 kHz		
1 mA	7.73	6.99		
10 mA	7.12	6.26		
250 mA	7.11	6.33		

Figure 27. Output Voltage Noise Spectral Density – V<sub>OUT</sub> = 1.8 V



	RMS Output Noise (μV)				
I <sub>OUT</sub>	10 Hz – 100 kHz	100 Hz – 100 kHz			
1 mA	7.9	7.07			
10 mA	7.19	6.25			
250 mA	7.29	6.38			

Figure 28. Output Voltage Noise Spectral Density – V<sub>OUT</sub> = 2.8 V

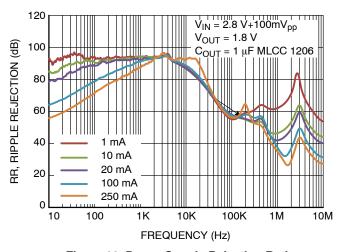


Figure 29. Power Supply Rejection Ratio –  $V_{OUT} = 1.8 \text{ V}$ 

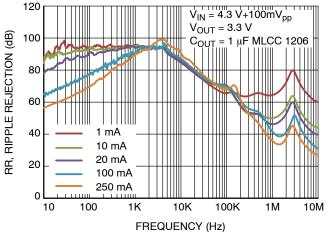


Figure 30. Power Supply Rejection Ratio – V<sub>OUT</sub> = 3.3 V

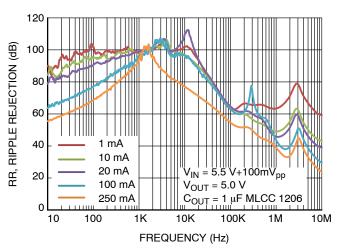


Figure 31. Power Supply Rejection Ratio –  $V_{OUT} = 5.0 \text{ V}$ 

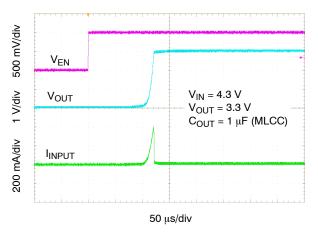


Figure 32. Enable Turn-on Response –  $C_{OUT}$  = 1  $\mu F$ ,  $I_{OUT}$  = 10 mA

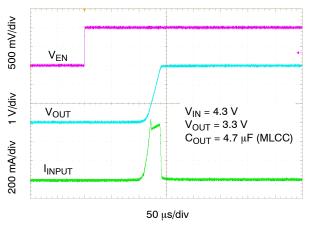


Figure 33. Enable Turn-on Response –  $C_{OUT}$  = 4.7  $\mu$ F,  $I_{OUT}$  = 10 mA

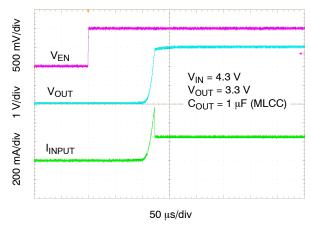


Figure 34. Enable Turn-on Response –  $C_{OUT}$  = 1  $\mu$ F,  $I_{OUT}$  = 250 mA

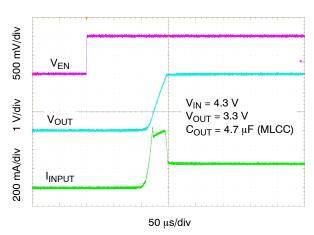


Figure 35. Enable Turn-on Response –  $C_{OUT}$  = 4.7  $\mu F$ ,  $I_{OUT}$  = 250 mA

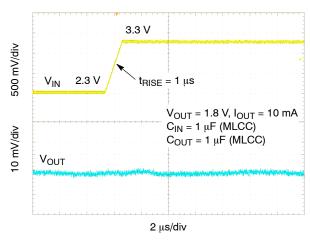


Figure 36. Line Transient Response –  $I_{OUT} = 10 \text{ mA}$ 

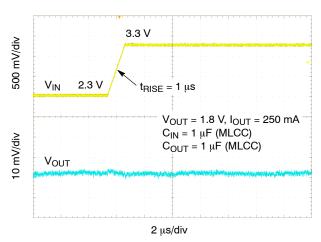


Figure 38. Line Transient Response – I<sub>OUT</sub> = 250 mA

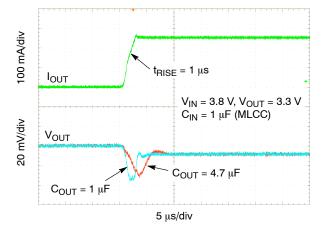


Figure 40. Load Transient Response – 1 mA to 250 mA

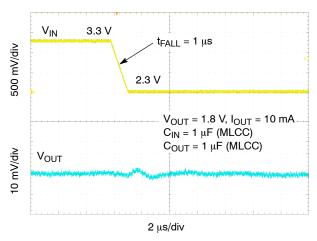


Figure 37. Line Transient Response –  $I_{OUT} = 10 \text{ mA}$ 

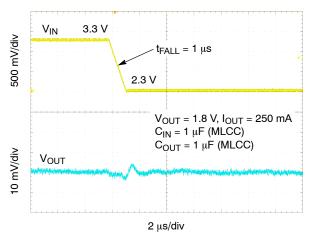


Figure 39. Line Transient Response – I<sub>OUT</sub> = 250 mA

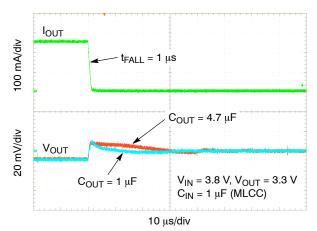


Figure 41. Load Transient Response – 250 mA to 1 mA

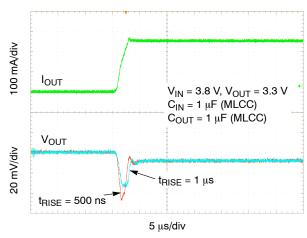


Figure 42. Load Transient Response – 1 mA to 250 mA

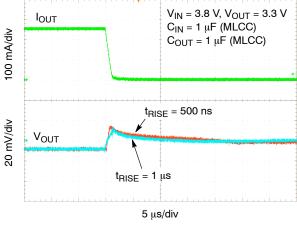


Figure 43. Load Transient Response – 250 mA to 1 mA

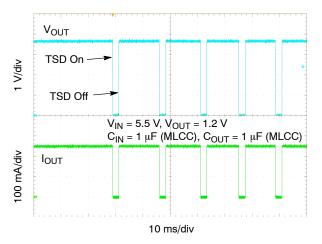


Figure 44. Overheating Protection – TSD

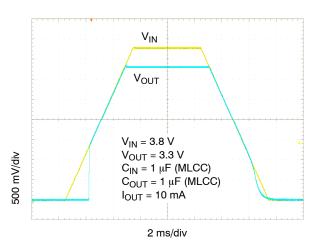


Figure 45. Turn-on/off - Slow Rising V<sub>IN</sub>

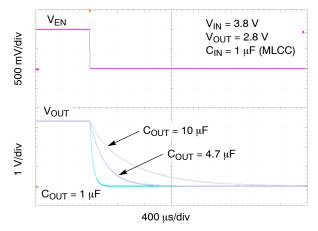


Figure 46. Enable Turn-off – Various Output Capacitors

#### **APPLICATIONS INFORMATION**

#### General

The SCV8163 is an ultra-low noise 250 mA low dropout regulator designed to meet the requirements of RF applications and high performance analog circuits. The SCV8163 device provides very high PSRR and excellent dynamic response. In connection with low quiescent current this device is well suitable for battery powered application such as cell phones, tablets and other. The SCV8163 is fully protected in case of current overload, output short circuit and overheating.

#### Input Capacitor Selection (CIN)

Input capacitor connected as close as possible is necessary for ensure device stability. The X7R or X5R capacitor should be used for reliable performance over temperature range. The value of the input capacitor should be 1  $\mu F$  or greater to ensure the best dynamic performance. This capacitor will provide a low impedance path for unwanted AC signals or noise modulated onto constant input voltage. There is no requirement for the ESR of the input capacitor but it is recommended to use ceramic capacitors for their low ESR and ESL. A good input capacitor will limit the influence of input trace inductance and source resistance during sudden load current changes.

# Output Decoupling (COUT)

The SCV8163 requires an output capacitor connected as close as possible to the output pin of the regulator. The recommended capacitor value is 1  $\mu F$  and X7R or X5R dielectric due to its low capacitance variations over the specified temperature range. The SCV8163 is designed to remain stable with minimum effective capacitance of 0.7  $\mu F$  to account for changes with temperature, DC bias and package size. Especially for small package size capacitors such as 0201 the effective capacitance drops rapidly with the applied DC bias. Please refer Figure 47.

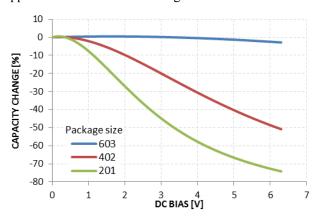


Figure 47. Capacity vs DC Bias Voltage

There is no requirement for the minimum value of Equivalent Series Resistance (ESR) for the  $C_{OUT}$  but the maximum value of ESR should be less than  $2\,\Omega$ . Larger output capacitors and lower ESR could improve the load

transient response or high frequency PSRR. It is not recommended to use tantalum capacitors on the output due to their large ESR. The equivalent series resistance of tantalum capacitors is also strongly dependent on the temperature, increasing at low temperature.

# **Enable Operation**

The SCV8163 uses the EN pin to enable/disable its device and to deactivate/activate the active discharge function.

If the EN pin voltage is <0.4 V the device is guaranteed to be disabled. The pass transistor is turned—off so that there is virtually no current flow between the IN and OUT. The active discharge transistor is active so that the output voltage  $V_{OUT}$  is pulled to GND through a 280  $\Omega$  resistor. In the disable state the device consumes as low as typ. 10 nA from the  $V_{IN}$ .

If the EN pin voltage >1.0 V the device is guaranteed to be enabled. The SCV8163 regulates the output voltage and the active discharge transistor is turned–off.

The EN pin has internal pull-down current source with typ. value of 200 nA which assures that the device is turned-off when the EN pin is not connected. In the case where the EN function isn't required the EN should be tied directly to IN.

# **Output Current Limit**

Output Current is internally limited within the IC to a typical 700 mA. The SCV8163 will source this amount of current measured with a voltage drops on the 90% of the nominal  $V_{OUT}$ . If the Output Voltage is directly shorted to ground ( $V_{OUT} = 0$  V), the short circuit protection will limit the output current to 690 mA (typ). The current limit and short circuit protection will work properly over whole temperature range and also input voltage range. There is no limitation for the short circuit duration.

# Thermal Shutdown

When the die temperature exceeds the Thermal Shutdown threshold ( $T_{SD}$  –  $160^{\circ}$ C typical), Thermal Shutdown event is detected and the device is disabled. The IC will remain in this state until the die temperature decreases below the Thermal Shutdown Reset threshold ( $T_{SDU}$  –  $140^{\circ}$ C typical). Once the IC temperature falls below the  $140^{\circ}$ C the LDO is enabled again. The thermal shutdown feature provides the protection from a catastrophic device failure due to accidental overheating. This protection is not intended to be used as a substitute for proper heat sinking.

# **Power Dissipation**

As power dissipated in the SCV8163 increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part.

The maximum power dissipation the SCV8163 can handle is given by:

$$P_{D(MAX)} = \frac{\left[125^{\circ}C - T_{A}\right]}{\theta_{1A}}$$
 (eq. 1)

The power dissipated by the SCV8163 for given application conditions can be calculated from the following equations:

$$P_D \approx V_{IN} \cdot I_{GND} + I_{OUT} (V_{IN} - V_{OUT})$$
 (eq. 2)

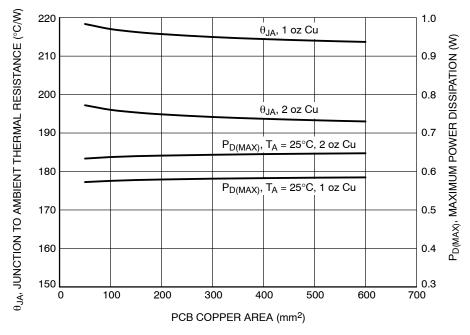


Figure 48.  $\theta_{JA}$  and  $P_{D\;(MAX)}$  vs. Copper Area

#### **Reverse Current**

The PMOS pass transistor has an inherent body diode which will be forward biased in the case that  $V_{OUT} > V_{IN}$ . Due to this fact in cases, where the extended reverse current condition can be anticipated the device may require additional external protection.

# **Power Supply Rejection Ratio**

The SCV8163 features very high Power Supply Rejection ratio. If desired the PSRR at higher frequencies in the range  $100~\rm kHz-10~MHz$  can be tuned by the selection of  $C_{OUT}$  capacitor and proper PCB layout.

### Turn-On Time

The turn-on time is defined as the time period from EN assertion to the point in which  $V_{OUT}$  will reach 98% of its nominal value. This time is dependent on various application conditions such as  $V_{OUT(NOM)}$ ,  $C_{OUT}$ ,  $T_A$ .

### **PCB Layout Recommendations**

To obtain good transient performance and good regulation characteristics place  $C_{\rm IN}$  and  $C_{\rm OUT}$  capacitors close to the device pins and make the PCB traces wide. In order to minimize the solution size, use 0402 or 0201 capacitors with appropriate capacity. Larger copper area connected to the pins will also improve the device thermal resistance. The actual power dissipation can be calculated from the equation above (Equation 2). Expose pad can be tied to the GND pin for improvement power dissipation and lower device temperature.

### **ORDERING INFORMATION**

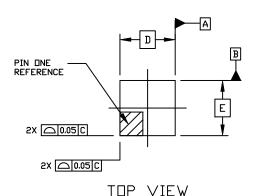
Device	Voltage Option	Marking	Description	Package	Shipping <sup>†</sup>
SCV8163AMX280TBG	2.8 V	NN	250 mA, Active Discharge	XDFN4 (Pb-Free)	3000 or 5000 / Tape & Reel (Note 7)

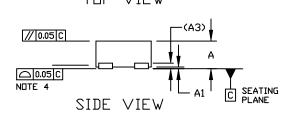
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

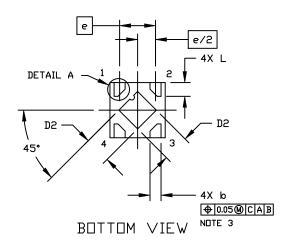
<sup>7.</sup> Product processed after October 1, 2022 are shipped with quantity 5000 units / tape & reel.

#### PACKAGE DIMENSIONS

# XDFN4 1.0x1.0, 0.65P CASE 711AJ ISSUE C

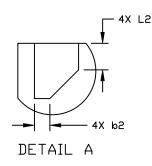




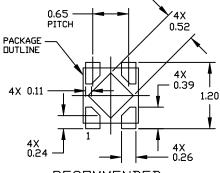


#### NOTES

- DIMENSIONING AND TOLERANCING PER. ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSION 6 APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 0.15 AND 0.20 FROM THE TERMINAL TIPS.
- 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.



WELL HS THE TENHINES						
	MILLIMETERS					
DIM	MIN	MIN NOM				
Α	0.33	0.38	0.43			
A1	0.00		0.05			
A3	0.10 REF					
b	0.15 0.20 0.25					
b2	0.02	0.07	0.12			
D	0.90	1.00	1.10			
D2	0.43 0.48 0.53					
Ε	0.90	1.00	1.10			
е	0.65 BSC					
L	0.20		0.30			
L2	0.07 0.17					



# RECOMMENDED MOUNTING FOOTPRINT

\* FOR ADDITIONAL INFORMATION ON OUR POFFRE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNT TECHNIQUES REFERENCE MANUAL, SOLDERRM/D

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